2SK2931

Silicon N Channel MOS FET High Speed Power Switching

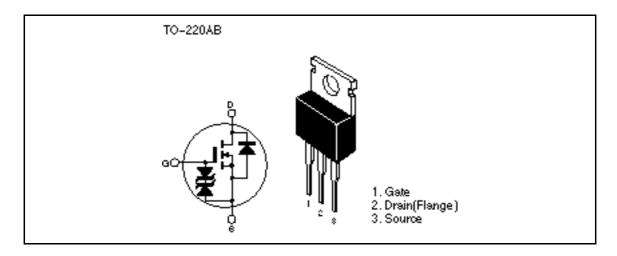
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ADE-208-554 Target Specification 1st. Edition

Features

- Low on-resistance
 - $R_{\rm DS}=0.010 \quad typ.$
- · High speed switching
- 4V gate drive device can be driven from 5V source

Outline





2SK2931

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	45	A
Drain peak current	L _{D(pulse)} *1	180	А
Body to drain diode reverse drain current	I _{DR}	45	А
Avalanche current	I _{AP} *3	45	Α
Avalanche energy	E _{AR} *3	173	mJ
Channel dissipation	Pch*2	75	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10µs, duty cycle 1 %

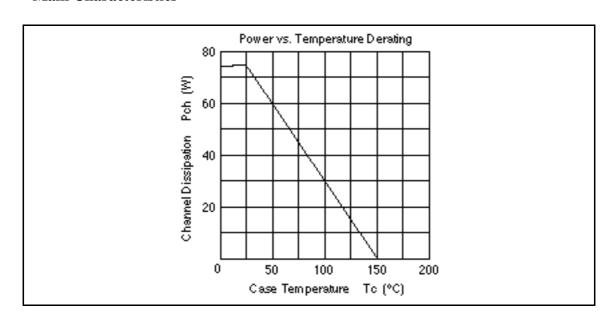
- 2. Value at $Tc = 25^{\circ}C$
- 3. Value at Tch = 25°C, Rg 50

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	_	_	V	$I_{D} = 10 \text{mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{G} = \pm 100 \mu A, V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16V, V_{DS} = 0$
Zero gate voltege drain current	I _{DSS}	_	_	10	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	_	2.5	V	$I_D = 1 \text{mA}, V_{DS} = 10 \text{V}$
Static drain to source on state	$R_{\scriptscriptstyle DS(on)}$	_	0.010	0.013		$I_D = 20A, V_{GS} = 10V^{*1}$
resistance	R _{DS(on)}	_	0.015	0.025		$I_D = 20A, V_{GS} = 4V^{*1}$
Forward transfer admittance	y _{fs}	24	40	_	S	$I_D = 20A, V_{DS} = 10V^{*1}$
Input capacitance	Ciss	_	2200	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	1050	_	pF	V _{GS} = 0
Reverse transfer capacitance	Crss	_	320	_	pF	f = 1MHz
Turn-on delay time	t _{d(on)}	_	25	_	ns	$I_{D} = 20A, V_{GS} = 10V$
Rise time	t _r	_	200	_	ns	R _L = 1.5
Turn-off delay time	$t_{d(off)}$	_	320	_	ns	
Fall time	t _f	_	240	_	ns	
Body to drain diode forward voltage	V_{DF}	_	0.95	_	V	$I_F = 45A, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	_	60	_	ns	$I_F = 45A, V_{GS} = 0$ diF/ dt = 50A/µs

Note: 1. Pulse test

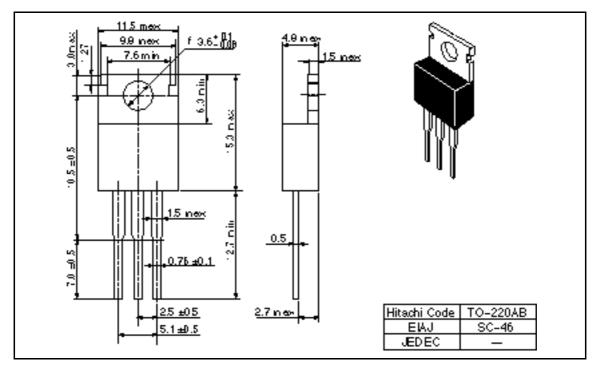
Main Characteristics



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Package Dimentions

Unit: mm



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Hitachi, Ltd. Semiconductor & IC Div. Nippon Bidg., 2-5-2, Ohte-medii, Chiyode-ku, Tokyo 100, Jepan Tat Tokyo (03, 3270-2111 Fax: (03, 3270-5109

For further in formation write to: Historia America, Utd. Semiconductor & IC Div. 2000 Sierra Point Perkway Briebene, CA. 94005-4835 USA

Tel: 415-589-8300 Fax: 415-583-4207 Hischi Burope GmbH
Bedronic Components Group
Cartinertal Burope
Darnscher Straße 3
D-85622 Feldkirchen
München
Tet 089-9 94 80-0
Fex: 089-9 29 30 00

Hitschi Burope Ltd.
Bedronic Components Div.
Northern Burope Headquerters
Whitebrook Ferk
Lower Cook hem Road
Maidenhead
Berkshire SL68YA
Urited Kingdom
Tet 0628-585000
Fex: 0628-178322

Hitschi Asia Pte. Ltd 45 Collyer Quey \$20-00 Hitschi Tower Snappore 0104 Tet 535-2100 Fex: 535-1533

Hischi Ásia (Hong Kong) Ltd. Unit 705, North Tower, World Finance Centra; Harbour City, Canton Road Teim Sha Telu, Kowloon Hang Kong Tet 27:350218 Fex: 27:30607 f